



# BDX53BFP

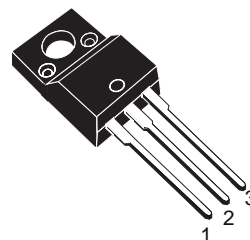
## SILICON POWER DARLINGTON TRANSISTOR

### APPLICATIONS:

- GENERAL PURPOSE SWITCHING AND AMPLIFIER
- LINEAR AND SWITCHING INDUSTRIAL EQUIPMENT
- FULLY INSULATED PACKAGE (U.L. COMPLIANT) FOR EASY MOUNTING

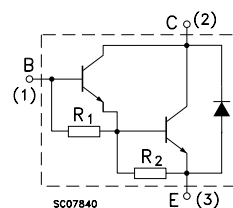
### DESCRIPTION

The BDX53BFP is a silicon Epitaxial-Base NPN power transistor in monolithic Darlington configuration mounted in T0-220FP fully molded isolated package. It is intended for use in hammer drivers, audio amplifiers and other medium power linear and switching applications.



T0-220FP

### INTERNAL SCHEMATIC DIAGRAM



R<sub>1</sub> Typ. = 10 K $\Omega$

R<sub>2</sub> Typ. = 150  $\Omega$

### ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V <sub>CBO</sub>	Collector-Base Voltage (I <sub>E</sub> = 0)	80	V
V <sub>CEO</sub>	Collector-Emitter Voltage (I <sub>B</sub> = 0)	80	V
V <sub>EBO</sub>	Emitter-base Voltage (I <sub>C</sub> = 0)	5	V
I <sub>C</sub>	Collector Current	8	A
I <sub>CM</sub>	Collector Peak Current (repetitive)	12	A
I <sub>B</sub>	Base Current	0.2	A
P <sub>tot</sub>	Total Dissipation at T <sub>c</sub> $\leq$ 25 °C	29	W
V <sub>isol</sub>	Insulation Withstand Voltage (RMS) from All Three Leads to External Heatsink	1500	V
T <sub>stg</sub>	Storage Temperature	-65 to 150	°C
T <sub>j</sub>	Max. Operating Junction Temperature	150	°C

BDX53BFP

THERMAL DATA

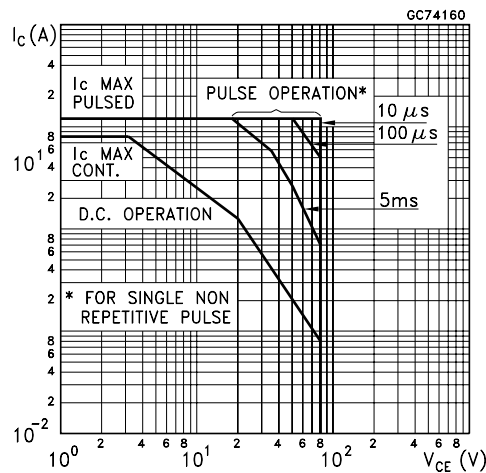
R <sub>thj-case</sub>	Thermal Resistance Junction-case	Max	4.3	°C/W
R <sub>thj-amb</sub>	Thermal Resistance Junction-ambient	Max	70	°C/W

ELECTRICAL CHARACTERISTICS (T<sub>case</sub> = 25 °C unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I <sub>CBO</sub>	Collector Cut-off Current (I <sub>E</sub> = 0)	V <sub>CB</sub> = 80 V			0.2	mA
I <sub>CEO</sub>	Collector Cut-off Current (I <sub>B</sub> = 0)	V <sub>CE</sub> = 40 V			0.5	mA
I <sub>EBO</sub>	Emitter Cut-off Current (I <sub>C</sub> = 0)	V <sub>EB</sub> = 5 V			2	mA
V <sub>CEO(sus)*</sub>	Collector-Emitter Sustaining Voltage (I <sub>B</sub> = 0)	I <sub>C</sub> = 100 mA	80			V
V <sub>CE(sat)*</sub>	Collector-emitter Saturation Voltage	I <sub>C</sub> = 3 A      I <sub>B</sub> = 12 mA			2	V
V <sub>BE(sat)*</sub>	Base-emitter Saturation Voltage	I <sub>C</sub> = 3 A      I <sub>B</sub> = 12 mA			2.5	V
h <sub>FE</sub> *	DC Current Gain	I <sub>C</sub> = 3 A      V <sub>CE</sub> = 3 V	750			
V <sub>F</sub> *	Parallel Diode Forward Voltage	I <sub>F</sub> = 3 A I <sub>F</sub> = 8 A		1.8 2.5	2.5	V V

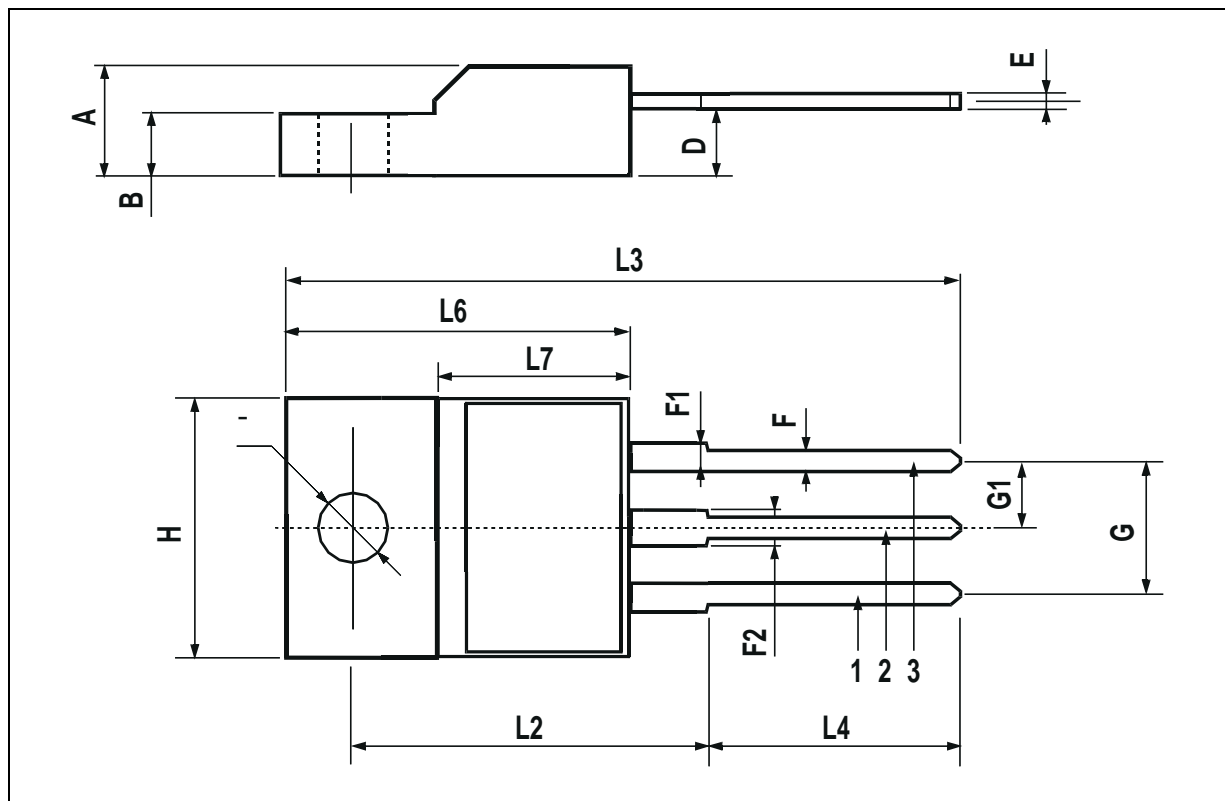
\* Pulsed: Pulse duration = 300 μs, duty cycle 1.5 %

Safe Operating Area



## TO-220FP MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.4		4.6	0.173		0.181
B	2.5		2.7	0.098		0.106
D	2.5		2.75	0.098		0.108
E	0.45		0.7	0.017		0.027
F	0.75		1	0.030		0.039
F1	1.15		1.7	0.045		0.067
F2	1.15		1.7	0.045		0.067
G	4.95		5.2	0.195		0.204
G1	2.4		2.7	0.094		0.106
H	10		10.4	0.393		0.409
L2		16			0.630	
L3	28.6		30.6	1.126		1.204
L4	9.8		10.6	0.385		0.417
L6	15.9		16.4	0.626		0.645
L7	9		9.3	0.354		0.366
Ø	3		3.2	0.118		0.126



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